LITE-ON SEMICONDUCTOR

MBR730 thru MBR760

SCHOTTKY BARRIER RECTIFIERS

REVERSE VOLTAGE **- 30** to **60** Volts
FORWARD CURRENT **- 7.5** Amperes

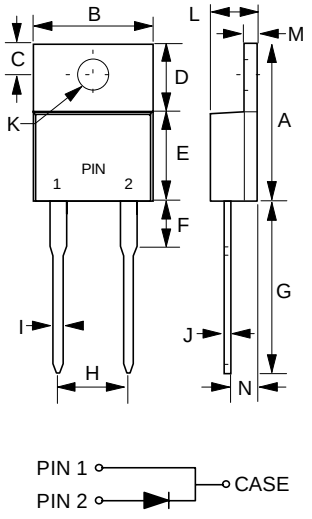
FEATURES

- Metal of silicon rectifier,majority carrier conducton
- Guard ring for transient protection
- Low power loss, high efficiency
- High current capability, low VF
- High surge capacity
- Plastic package has UL flammability classification 94V-0
- For use in low voltage,high frequency inverters,free whelling,and polarity protection applications

MECHANICAL DATA

- Case : TO-220AC molded plastic
- Polarity : As marked on the body
- Weight : 0.08 ounces, 2.24 grams
- Mounting position : Any

TO-220AC



TO-220AC		
DIM.	MIN.	MAX.
A	14.22	15.88
B	9.65	10.67
C	2.54	3.43
D	5.84	6.86
E	8.26	9.28
F	-	6.35
G	12.70	14.73
H	4.83	5.33
I	0.51	1.14
J	0.30	0.64
K	3.53 ∅	4.09 ∅
L	3.56	4.83
M	1.14	1.40
N	2.03	2.92
All Dimensions in millimeter		

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.
Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	MBR730	MBR735	MBR740	MBR745	MBR750	MBR760	UNIT
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	30	35	40	45	50	60	V
Maximum RMS Voltage	V_{RMS}	21	24.5	28	31.5	35	42	V
Maximum DC Blocking Voltage	V_{DC}	30	35	40	45	50	60	V
Maximum Average Forward Rectified Current (See Fig.1) @T_C=125˚C	$I_{(AV)}$	7.5						A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	150						A
Voltage Rate of Change (Rated VR)	dv/dt	10000						V/us
Maximum Forward Voltage (Note 1) I_F=7.5A @ T_J=25˚C I_F=7.5A @ T_J=125˚C I_F=15A @ T_J=25˚C I_F=15A @ T_J=125˚C	V_F	-	0.57	0.84	0.72	0.75	0.65	-	-	V
Maximum DC Reverse Current at Rated DC Blocking Voltage @T_J=25˚C @T_J=125˚C	I_R	0.1	15			0.5	50			mA
Typical Thermal Resistance (Note 2)	$R_{\theta JC}$	3.5						˚C/W
Typical Junction Capacitance (Note 3)	C_J	400						pF
Operating Temperature Range	T_J	-55 to +150						˚C
Storage Temperature Range	T_{STG}	-55 to +175						˚C

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NOTES : 1. 300us Pulse Width, Duty Cycle 2%
2. Thermal Resistance Junction to Case.
3. Measured at 1.0MHz and Applied Reverse Voltage of 4.0V DC.

FIG.1 - FORWARD CURRENT DERATING CURVE

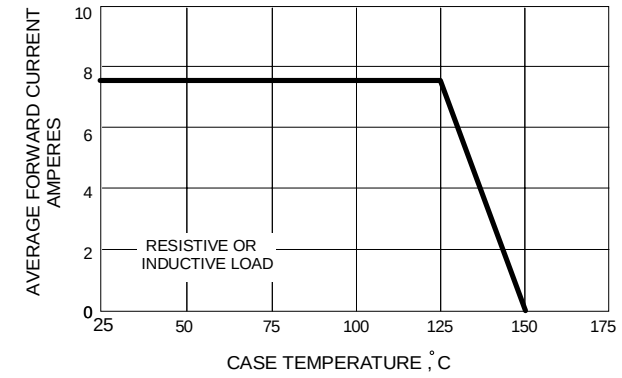

FIG.2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

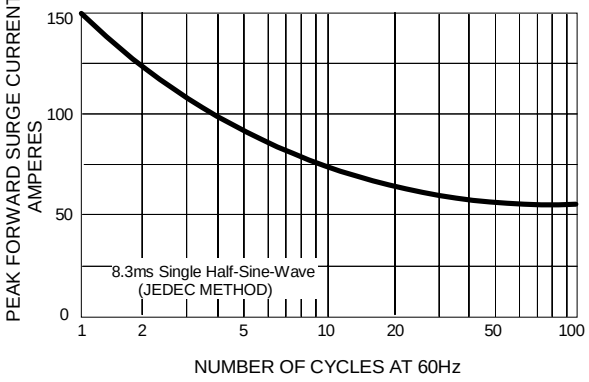

FIG.3 - TYPICAL REVERSE CHARACTERISTICS

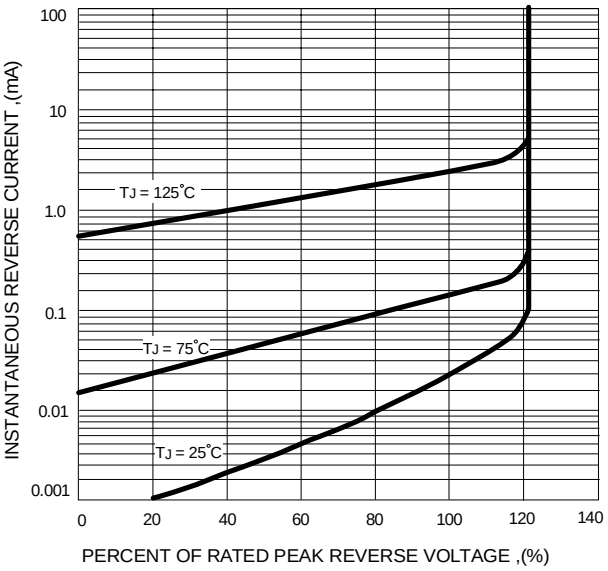

FIG.4 - TYPICAL FORWARD CHARACTERISTICS

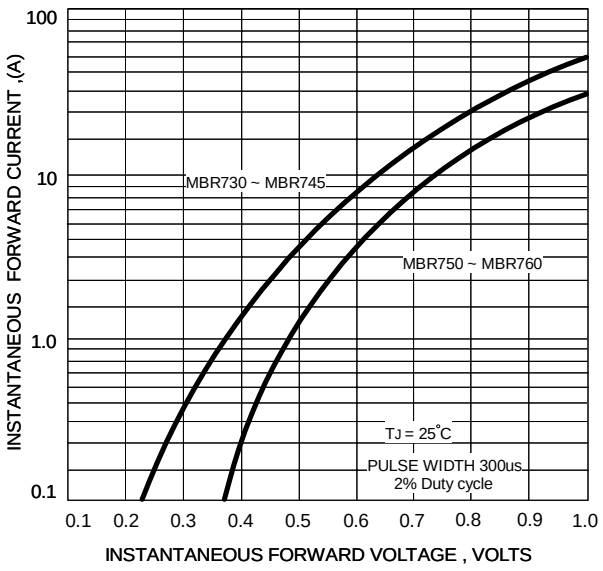

FIG.5 - TYPICAL JUNCTION CAPACITANCE